

Supporting Information

Potential Applications of Halide Double Perovskite $\text{Cs}_2\text{AgInX}_6$ ($\text{X} = \text{Cl}, \text{Br}$) in Flexible Optoelectronics: Unusual Effects of Uniaxial Strains

Zhao Zhang, Jie Su, Jie Hou, Zhenhua Lin, Zhaosheng Hu, Jingjing Chang*, Jincheng Zhang, and Yue Hao*

China State Key Discipline Laboratory of Wide Band Gap Semiconductor Tecchnology,
Shaanxi Joint Key Laboratory of Graphene, Advanced Interdisciplinary Research Center for
Flexible Electronics, School of Microelectronics, Xidian University, Xi'an, 710071, China.

*E-mail: sujie@xidian.edu.cn; jjingchang@xidian.edu.cn

Table S1. Lattice constants ($a=b=c$) (in unit of Å) obtained by different methods, and bond lengths (in unit of Å), elastic constants (in unit of N/m) and band gaps (in unit of eV) calculated by LDA method for $\text{Cs}_2\text{AgInX}_6$ ($X = \text{Cl}, \text{Br}$). For comparison, the values calculated from previous studies and experiments are also listed.

	Lattice constant						Bond length		Elastic constant	Band gap
	LDA	Experiment	HSE	PBE	PW91	PBE0	In-X	Ag-X		
$\text{Cs}_2\text{AgInCl}_6$	10.22, 10.2 ¹	10.47	10.62 ¹	10.65 ¹	10.65	10.68	2.51	2.59	71.02	0.65, 2.1-3.3 ¹
$\text{Cs}_2\text{AgInBr}_6$	11.43, 11.16 ² , 11.20 ³		11.20 ⁴	11.60	11.60	11.58	2.81	2.90	67.73	0.58 1.5 ² , 1.33 ³

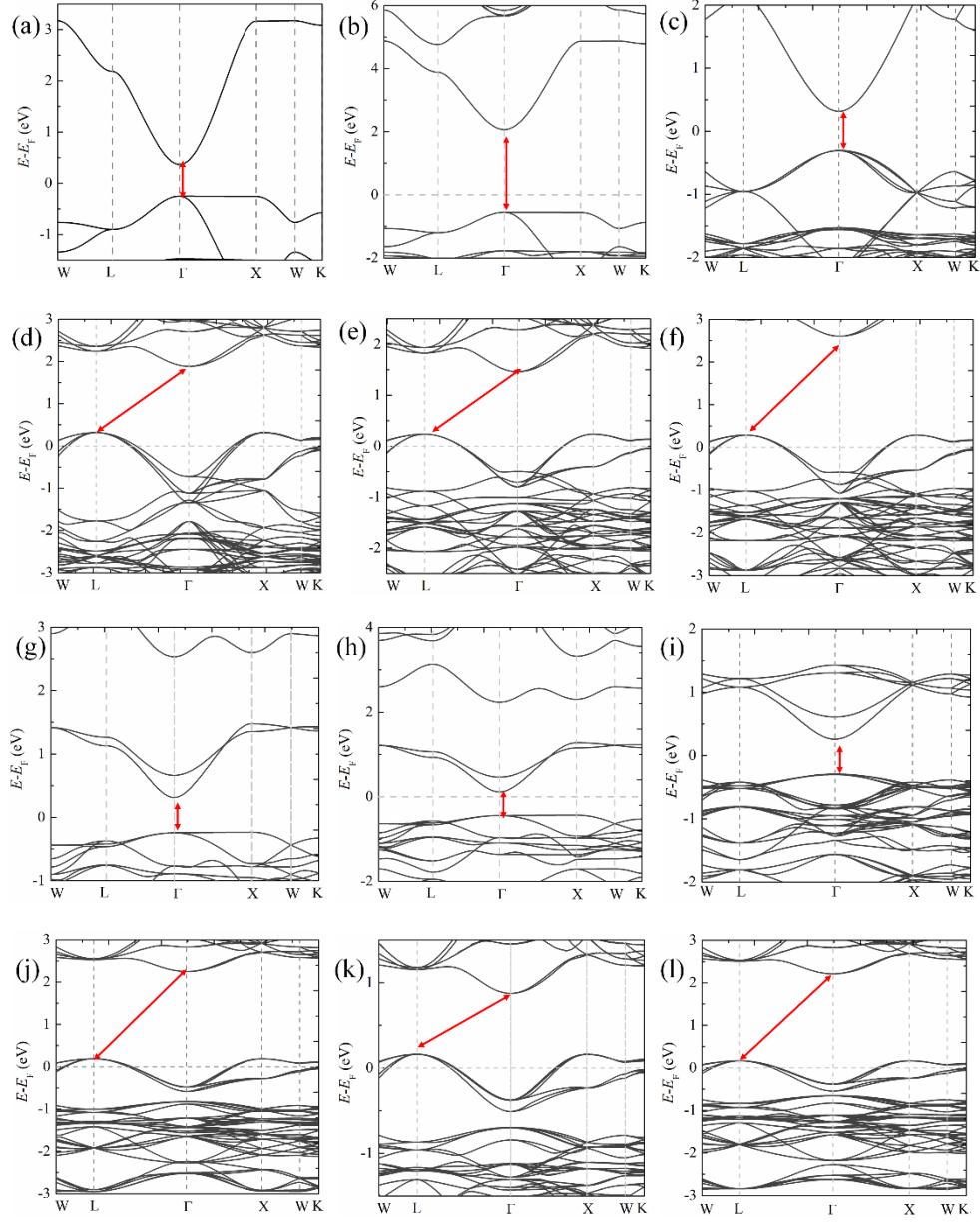


Figure S1. Band structures of $\text{Cs}_2\text{AgInCl}_6$ primitive cell obtained by (a) LDA and (b) HSE functionals, respectively. Band structures of $\text{Cs}_2\text{AgInCl}_6$ unit-cell obtained by (c) LDA, (d) GGA-PBE, (e) PBE0, (f) GGA-PW91 methods, respectively. Band structures of $\text{Cs}_2\text{AgInBr}_6$ primitive cell obtained by (g) LDA and (h) HSE functionals, respectively. Band structures of $\text{Cs}_2\text{AgInBr}_6$ unit-cell obtained by (i) LDA, (j) GGA-PBE, (k) PBE0, (l) GGA-PW91 methods, respectively.

It can be found that the band structures of $\text{Cs}_2\text{AgInX}_6$ ($\text{X}=\text{Cl}, \text{Br}$) calculated by

GGA-PBE, GGA-91, PBE0 methods show indirect band gap characters, which is inconsistent with previous reports ^{1,4,5}. That is because band edges of Cs₂AgInX₆ (X=Cl, Br) are sensitive to the lattice constants (such phenomenon is analyzed in detail in the following section) which are difficult to be accurately obtained by these methods, as listed in Table S1. While the band structures of Cs₂AgInX₆ (X=Cl, Br) perovskite obtained by LDA and HSE corrected methods ^{1,4,5} are similar, except for the band gaps, suggesting that LDA method is sufficient to understand the electronic properties of Cs₂AgInX₆ (X=Cl, Br) perovskite. Thus, the physical properties, except for the band gap, of Cs₂AgInX₆ (X=Cl, Br) in the following section are calculated by LDA method.

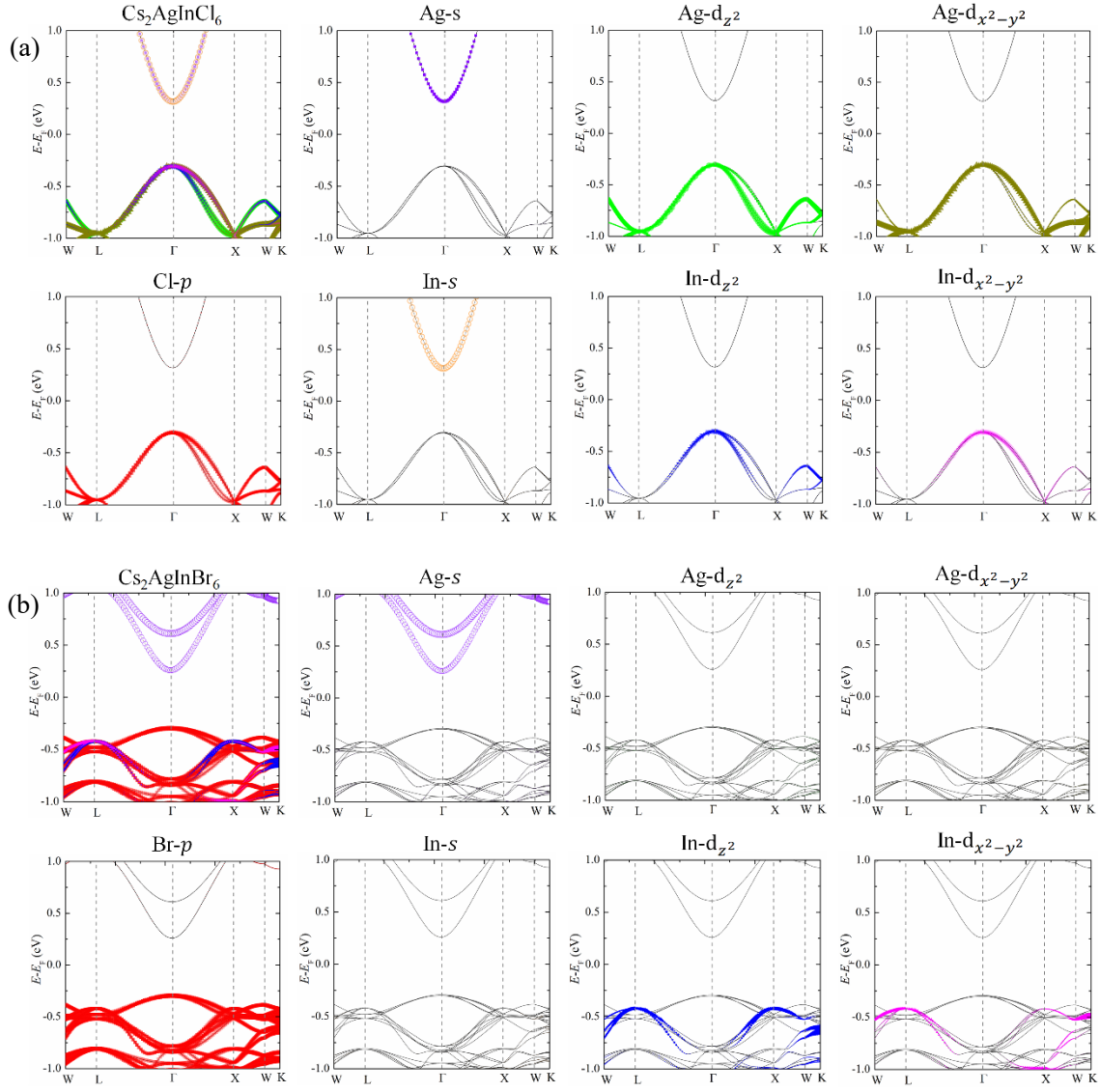


Figure S2. Orbital-projected band structures for (a) pure $\text{Cs}_2\text{AgInCl}_6$ and (b) pure $\text{Cs}_2\text{AgInBr}_6$. The vertical color belt represents the strength of corresponding orbital contributions.

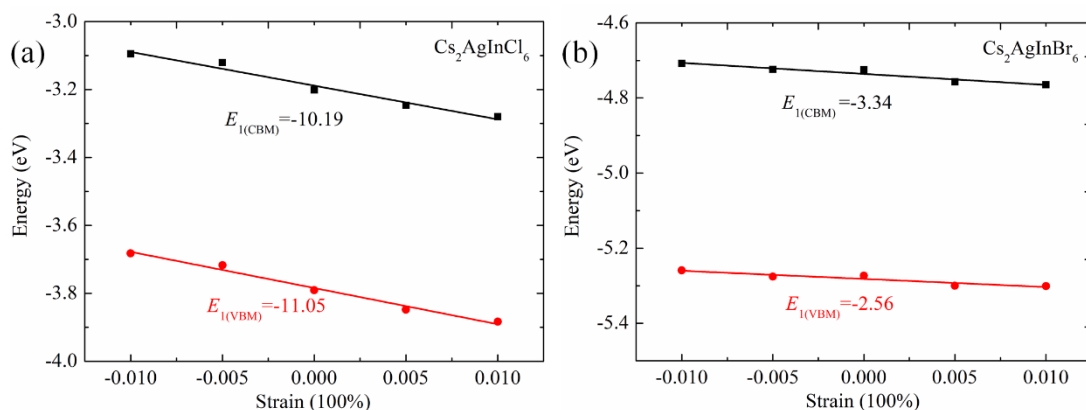


Figure S3. Energy shifts of CBM and VBM of (a) $\text{Cs}_2\text{AgInCl}_6$ and (b) $\text{Cs}_2\text{AgInBr}_6$ under strains, respectively. The slopes of these lines are the corresponding deformation potentials.

References

- (1) Volonakis, G.; Haghighirad, A. A.; Milot, R. L.; Sio, W. H.; Filip, M. R.; Wenger, B.; Johnston, M. B.; Herz, L. M.; Snaith, H. J.; Giustino, F. $\text{Cs}_2\text{InAgCl}_6$: A New Lead-Free Halide Double Perovskite with Direct Band Gap. *J. Phys. Chem. Lett.* **2017**, *8*, 772–778.
- (2) Zhao, X.-G.; Yang, D.; Sun, Y.; Li, T.; Zhang, L.; Yu, L.; Zunger, A. Cu–In Halide Perovskite Solar Absorbers. *J. Am. Chem. Soc.* **2017**, *139*, 6718–6725.
- (3) Volonakis, G.; Giustino, F. Surface Properties of Lead-Free Halide Double Perovskites: Possible Visible-Light Photo-Catalysts for Water Splitting. *Appl. Phys. Lett.* **2018**, *112*, 243901.
- (4) Xu, J.; Liu, J.-B.; Liu, B.-X.; Huang, B. Intrinsic Defect Physics in Indium-Based Lead-Free Halide Double Perovskites. *J. Phys. Chem. Lett.* **2017**, *8*, 4391–4396.
- (5) Li, T.; Zhao, X.; Yang, D.; Du, M.-H.; Zhang, L. Intrinsic Defect Properties in Halide Double Perovskites for Optoelectronic Applications. *Phys. Rev. Appl.* **2018**, *10*, 041001.